



1N 6263

SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

Metal to silicon junction diode featuring high breakdown, low turn-on voltage and ultrafast switching. Primarily intended for high level UHF/VHF detection and pulse application with broad dynamic range.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage	60	V
I _F	Forward Continuous Current*	T _a = 25 °C	15 mA
I _{FSM}	Surge non Repetitive Forward Current*	t _p ≤ 1s	50 mA
T _{stg} T _j	Storage and Junction Temperature Range	- 65 to 200 - 65 to 200	°C
T _L	Maximum Lead Temperature for Soldering during 10s at 4mm from Case	230	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-a)}	Junction-ambient*	400	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR}	T _{amb} = 25°C I _R = 10µA	60			V
V _F **	T _{amb} = 25°C I _F = 1mA			0.41	V
	T _{amb} = 25°C I _F = 15mA			1	
I _R **	T _{amb} = 25°C V _R = 50V			0.2	µA

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions	Min.	Typ.	Max.	Unit
C	T _{amb} = 25°C V _R = 0V f = 1MHz			2.2	pF
τ	T _{amb} = 25°C I _F = 5mA Krakauer Method			100	ps

* On infinite heatsink with 4mm lead length

** Pulse test: t_p ≤ 300µs δ < 2%.

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.



Fig.1 : Forward current versus forward voltage (typical values).

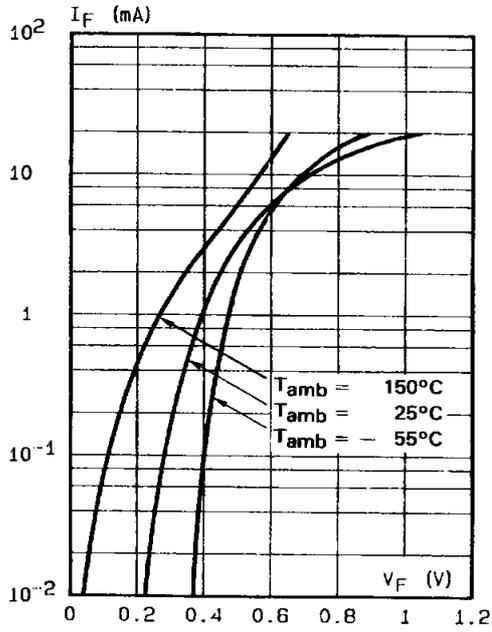


Fig.2 : Capacitance C versus reverse applied voltage V_R (typical values).

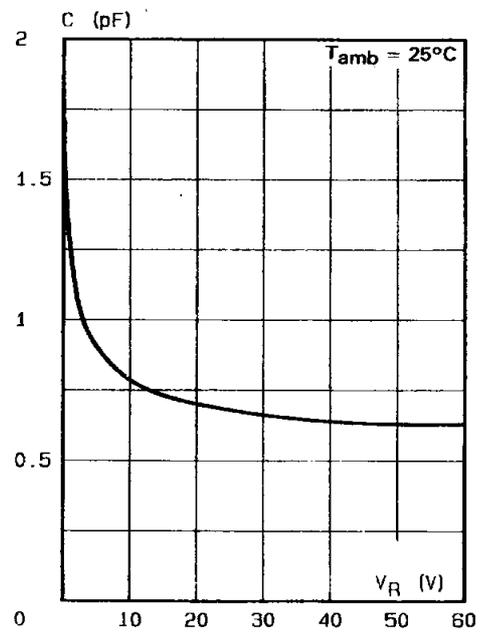


Fig.3 : Reverse current versus ambient temperature.

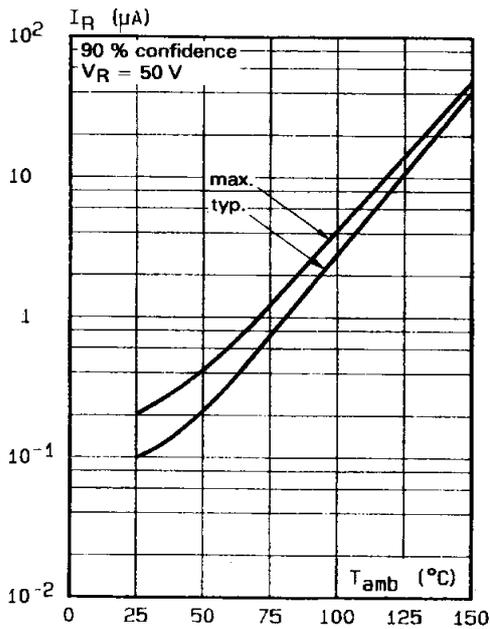
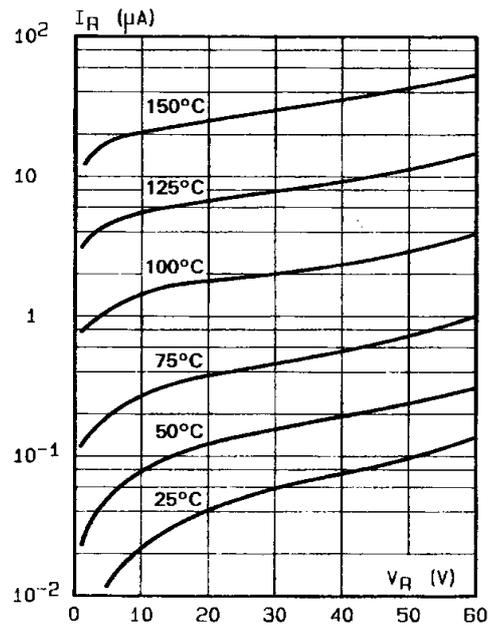
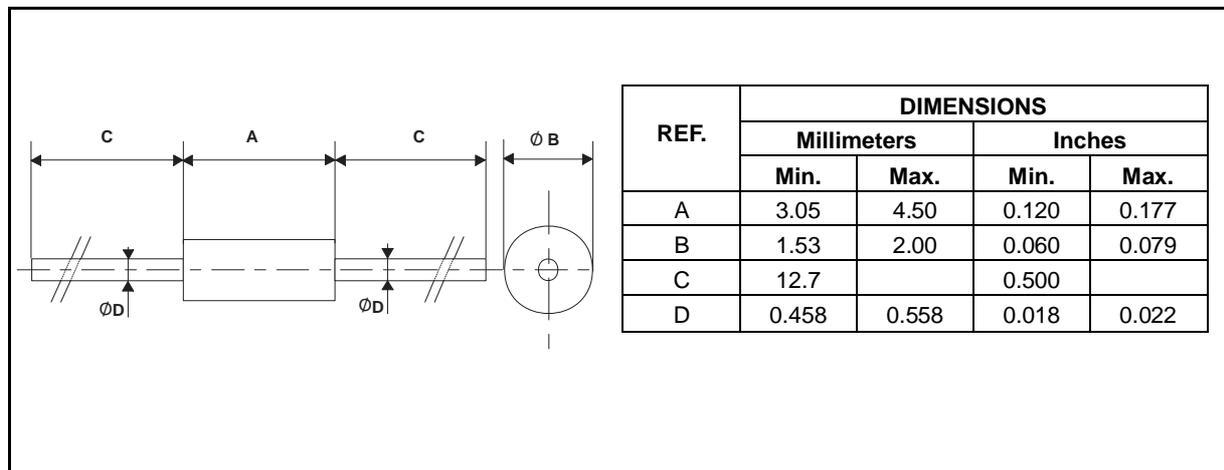


Fig.4 : Reverse current versus continuous reverse voltage (typical values).



PACKAGE MECHANICAL DATA

DO 35 Glass



Cooling method : by convection and conduction
 Marking: clear, ring at cathode end.
 Weight: 0.15g

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